a perforated plasma confinement ring disposed outside of an outer periphery of said bottom electrode, a top surface of said perforated plasma confinement ring being disposed below a top surface of said substrate, said perforated plasma confinement ring being **formed from a** conductive **material** and **[said perforated plasma confinement ring being]** electrically grounded during said processing **so as to increase ion energy during said processing**.

16. Cancelled

17. (Once amended) The plasma processing reactor of claim 14 wherein said perforated plasma confinement ring perforations are slotted perforations**, which are linear and radially positioned relative to the center of said perforated plasma confinement ring**.

18. Cancelled

20. Cancelled

24. (Twice amended) A perforated plasma confinement ring device configured to be disposed inside a plasma processing reactor during processing, comprising:

a conductive ring having an inner and outer diameter, said inner diameter being dimensioned to surround a bottom electrode in said plasma processing reactor, said bottom electrode providing support for a substrate to be processed, said bottom electrode being coupled to a first RF source having a first RF frequency, said bottom electrode being spaced apart from a top electrode, said top electrode being coupled to a second RF source having a second RF frequency, said second RF frequency being greater than said first RF frequency, said conductive ring **being formed from a conductor that is substantially resistant to etching by said plasma present within said chamber during said processing, said conductive ring** being electrically grounded during said processing, said conductive ring having therein a plurality of perforations, said plurality of perforations being dimensioned to permit by-product gases from said processing to pass through while substantially confining a plasma to the upstream side of said conductive ring, and said conductive ring removing electrons from said plasma and thereby increasing ion energy in said plasma.

26. Cancelled.

(Once amended) The perforated plasma confinement ring of claim ~~24~~ wherein said perforated plasma confinement ring perforations are slotted perforations**, which are positioned orthogonal relative to the inner and outer diameter of the perforated plasma confinement ring**.

Please **ADD** claims 35-38 as follows:

35. (New) A perforated plasma confinement ring for containing a plasma inside a process chamber of a plasma processing reactor during processing of a substrate, the perforated confinement ring being disposed between a bottom electrode and a side wall of said process chamber, the perforated plasma confinement ring comprising:

a conductive ring having an inner periphery dimensioned to surround said bottom electrode in said plasma processing reactor, said conductive ring being formed from a conductor that is substantially resistant to etching by said plasma present within said chamber during said processing, said conductive ring being electrically grounded during said processing, said conductive ring having therein a plurality of perforations, said plurality of perforations being dimensioned to permit by-product gases from said processing to pass through while substantially confining said plasma to the upstream side of said conductive ring.

36. (New) The perforated plasma confinement ring of claim ~~35~~ wherein the conductive ring is formed from SiC.

37. (New) The perforated plasma confinement ring of claim 1 wherein the conductive ring is formed from SiC.

38. (New) The perforated plasma confinement ring of claim ~~24~~ wherein the conductive ring is formed from SiC.